

# Final Report for ECG 620 (OpAmp Project)

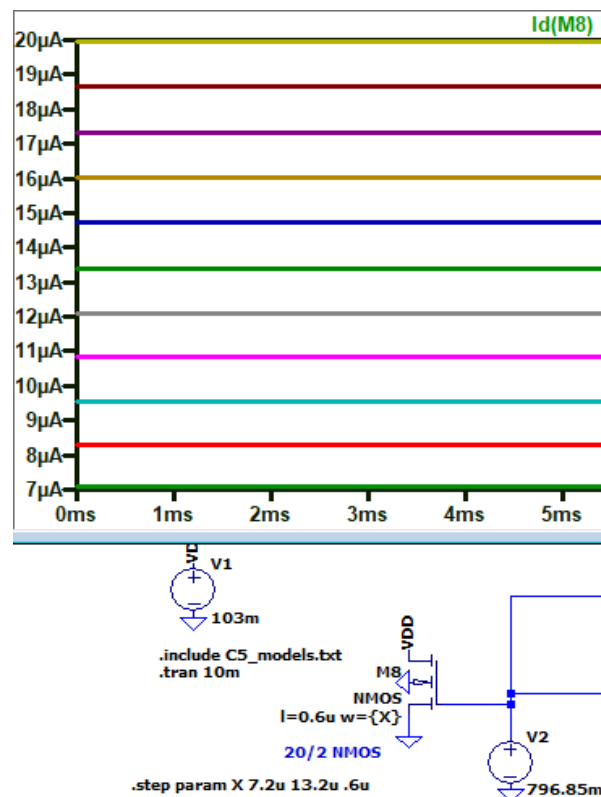
May 8<sup>th</sup>, 2019  
By Jason Silic

## Introduction

The project specifications were not completely satisfied with PSRR and CMRR being the biggest culprits. However, the Gain-Bandwidth product is excellent. The use of a more sophisticated topology, such as those utilizing OTAs, would assuredly improve the situation. In addition, I believe power draw is rather large. The final OpAmp schematic is in **OpAmpBeta2.asc**.

## Design Process

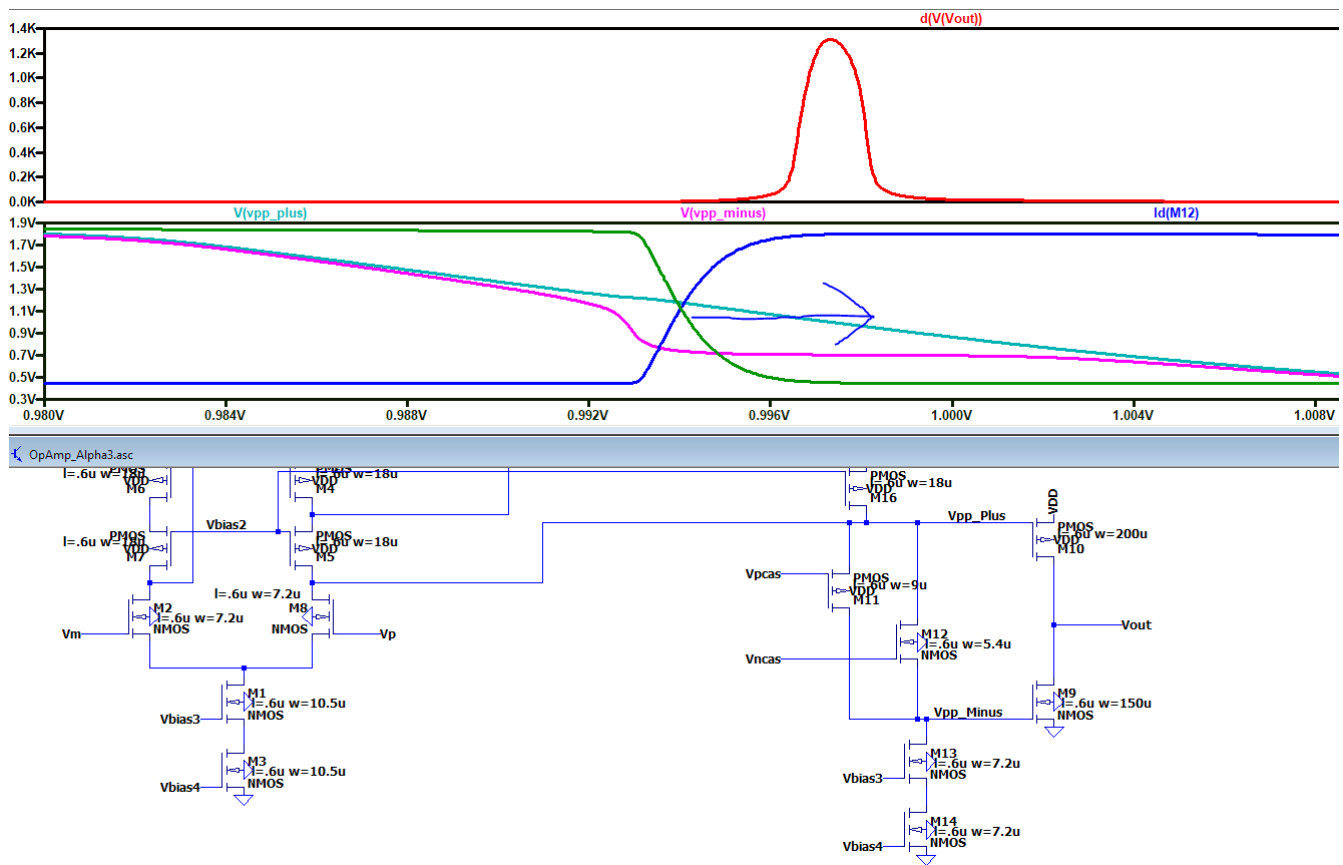
The first step in the project design was to select appropriate sizes for the biasing circuit. This requires that threshold voltages be determined. From the C5\_models.txt file values of  $V_{THN} = 0.67V$  and  $V_{THP} = 0.92V$  were chosen. (Later, more precise values of  $V_{thn}=0.64V$ ,  $V_{thp}=0.86V$  were determined by simulating and determining gate-source voltage when  $1\mu A$  of drain current flows.) An overdrive voltage of  $60mV$  and a target current of  $8\mu A$  were used to select standard widths of NMOS and PMOS transistors. (Length was always standard  $2 \cdot scale = 0.6\mu m$ .) The testing circuit can be seen in BetaTestNMOS2.asc and BetaTestPMOS2.asc. **Figure 1** is an example simulation from previous:



I believe Alpha1 and Alpha2 OpAmp circuits are from this stage of the design, where it became clear that more gain was required. The bias circuit was redesigned with first  $5\mu\text{A}$ , then finally about  $2\mu\text{A}$  of current per branch and ostensibly about  $50\text{mV}$  of overdrive voltage. This led to sizes of  $.6\mu/12\mu$  for NMOS and  $.6\mu/30\mu$  for PMOS. Designing the BMR is tricky when close to the subthreshold region as current does not scale linearly with width, as our equations would expect. Design is mostly choose  $k=4$  (final design,  $k=3$ ) and plug in a good resistor value by experimentation.

A few other notes about the reference relate to how I tried to obtain more gain. Note in Fig 2 below how the floating current mirror is not active exactly where the region of maximum gain exists.

Figure 2

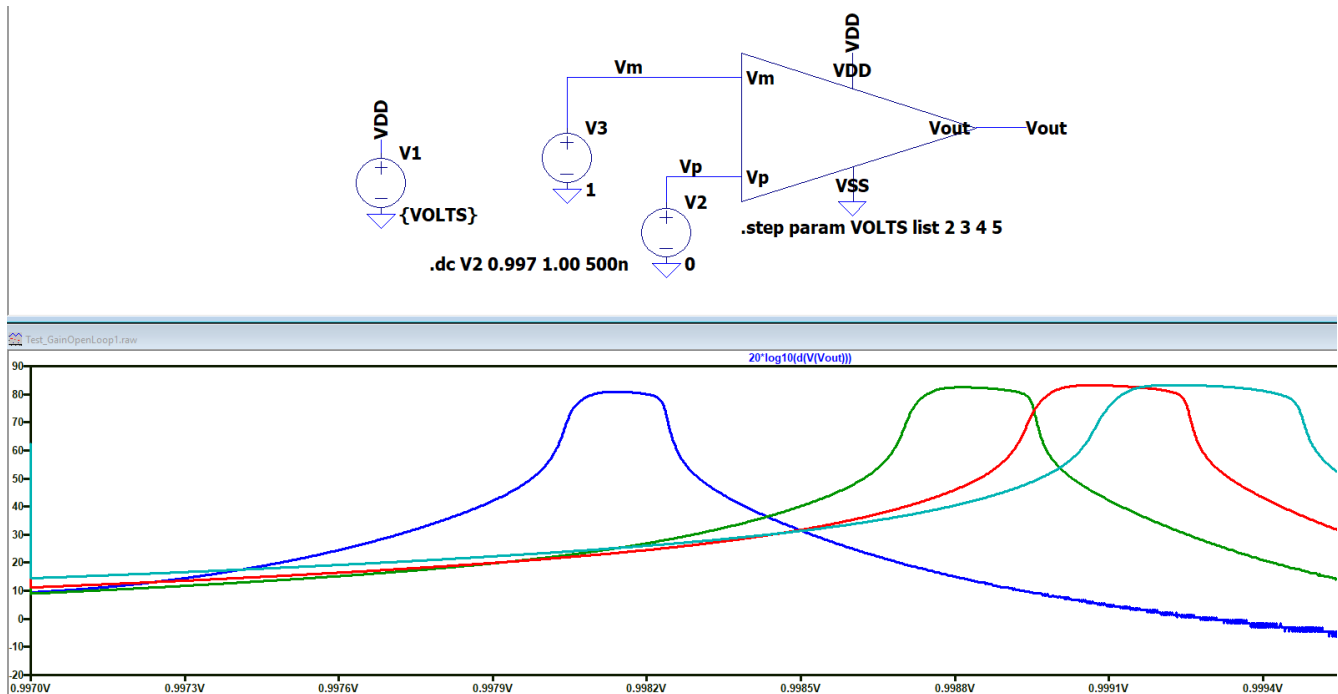


One method employed to improve gain is to move the  $Vpp\_Minus$  node lower. This is achieved by lowering the  $Vncas$  voltage. Note in the C5Reference.asc circuit that M30, used to generate  $Vncas$ , is extremely wide.  $Vbias2$  was also tweaked in this manner to be a bit lower.

### Specifications

The original specification calls for  $80\text{dB}$  of gain at voltages between 2 and 5 volts. This specification is met in figure 3.

Figure 3

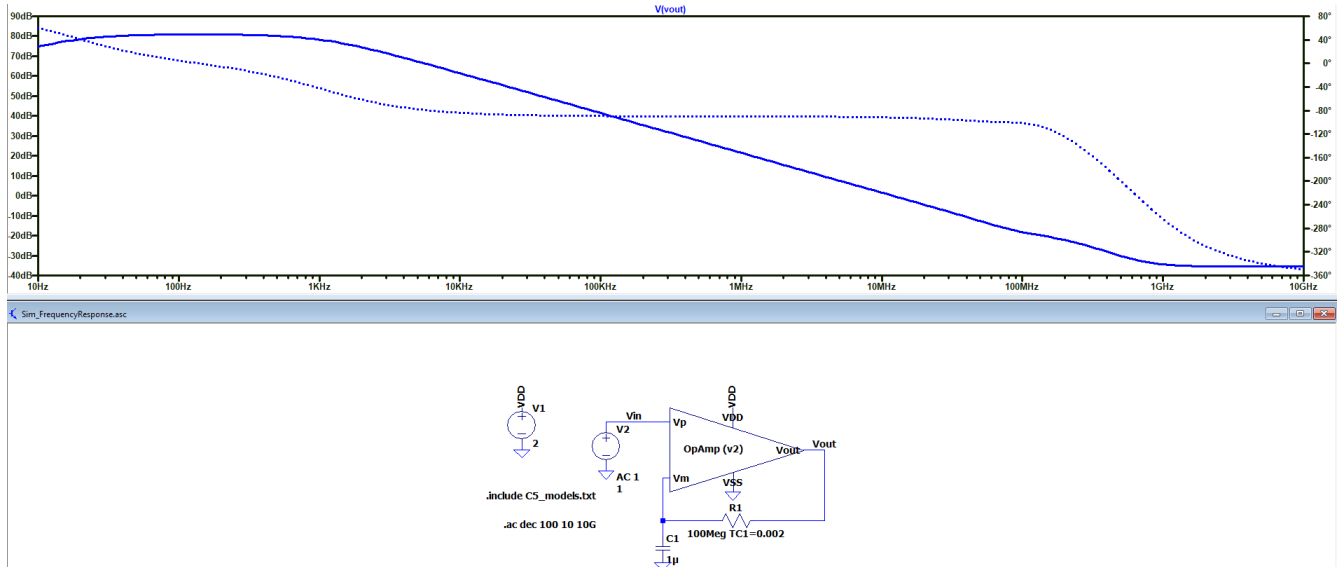


The most difficult part of the compensation design (aside from understanding it) was getting capacitance values. Looking in the C5\_models.txt file we see that  $t_{ox} = 1.39 \times 10^{-8} \text{m}$ .  $C_{ox}' = [\epsilon_{SiO_2}] \cdot 3.9 / t_{ox}$ , where 3.9 is relative permittivity of SiO<sub>2</sub>:  $(8.85 \times 10^{-12}) \cdot 3.9 / 1.39 \times 10^{-8} = 2.48 \text{fF}/\mu\text{m}^2$ .  $C_{gs}' = 2/3 \cdot 2.48 \text{fF}/\mu\text{m}^2 \cdot 0.6 \mu\text{m} = 0.99 \text{fF}/\mu\text{m}$ . Cgd involves CGDO parameters, and finally:  $C_{gd}' = 0.2 \text{fF}/\mu\text{m}$  (of width, NMOS) and  $C_{gd}' = 0.29 \text{fF}/\mu\text{m}$  (PMOS). We perform simulations to determine transconductance and resistance parameters of gm1, gm2, R1, R2:  $C_1 = 161 \text{fF} = C_{gd}(M_5) + C_{gd}(M_8, \text{with miller effect gain of } 59)$ .  $C_2 = \text{small} + \text{load}$ .  $C_c = \text{at least } 174 \text{fF}$ .  $R_1 = 1.3 \text{M}$ ,  $R_2 = 932$  (but I actually decreased size of output buffer after this, so these values are not completely correct),  $g_{m1} = 48 \mu\text{A}/\text{V}$ ,  $g_{m2} \approx 10 \text{mA}/\text{V}$  (estimated with **Sim\_gm1.asc**, **Sim\_ro2.asc**, and related circuits).

Results:  $f_z = 9 \text{GHz}$ ,  $f_1 = 75 \text{kHz}$ ,  $f_2 = 2 \text{GHz}$ . A random 1pF capacitor was added as compensation and did not seem to cause much harm.

In Fig. 4 we can see the frequency response meets the requirement of 1MHz Gain-Bandwidth Product as the unity-gain frequency is about 11MHz.

Figure 4



Other parameters

Power Supply Rejection Ratio unfortunately did not meet specifications. The next figure shows PSRR- is not working very well.

Figure 5

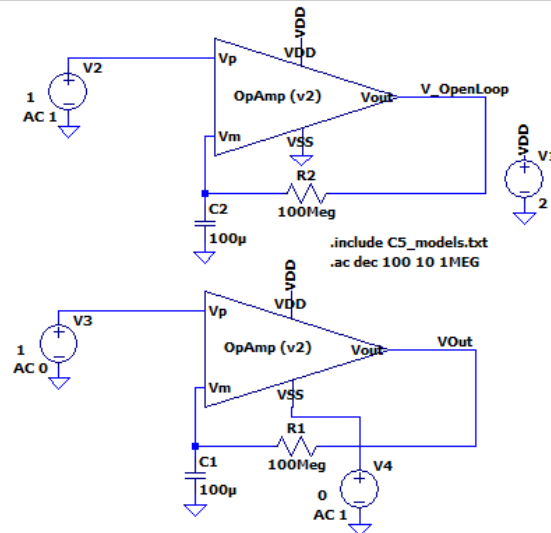
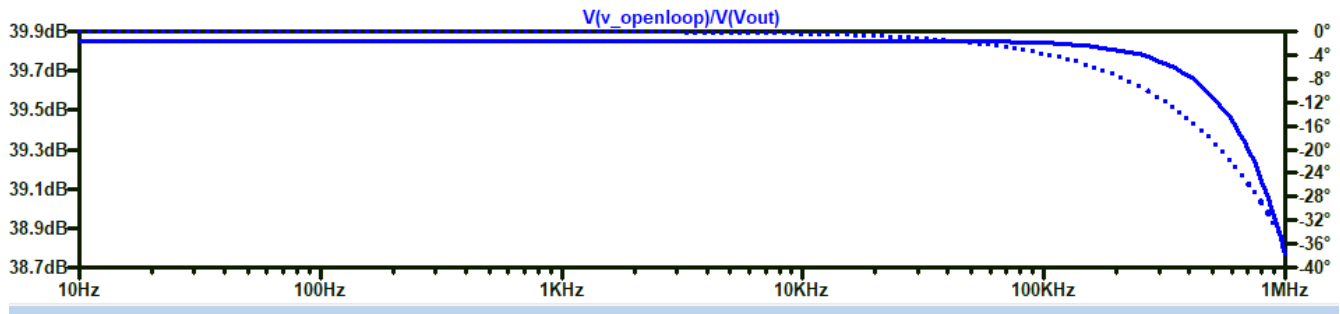
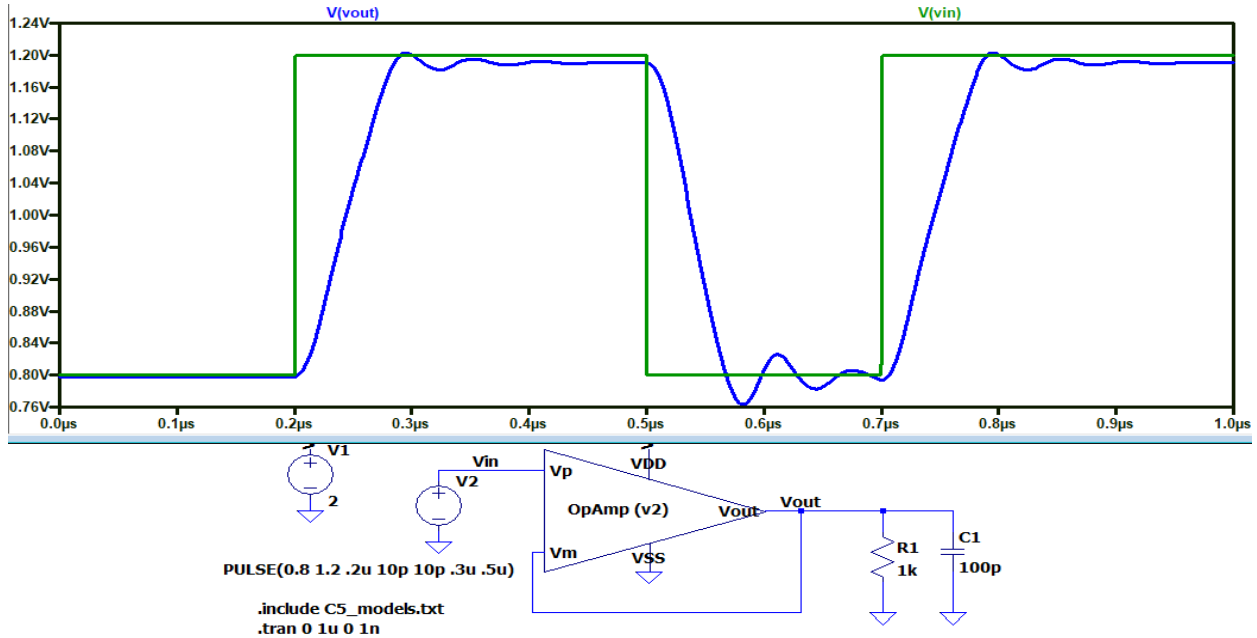
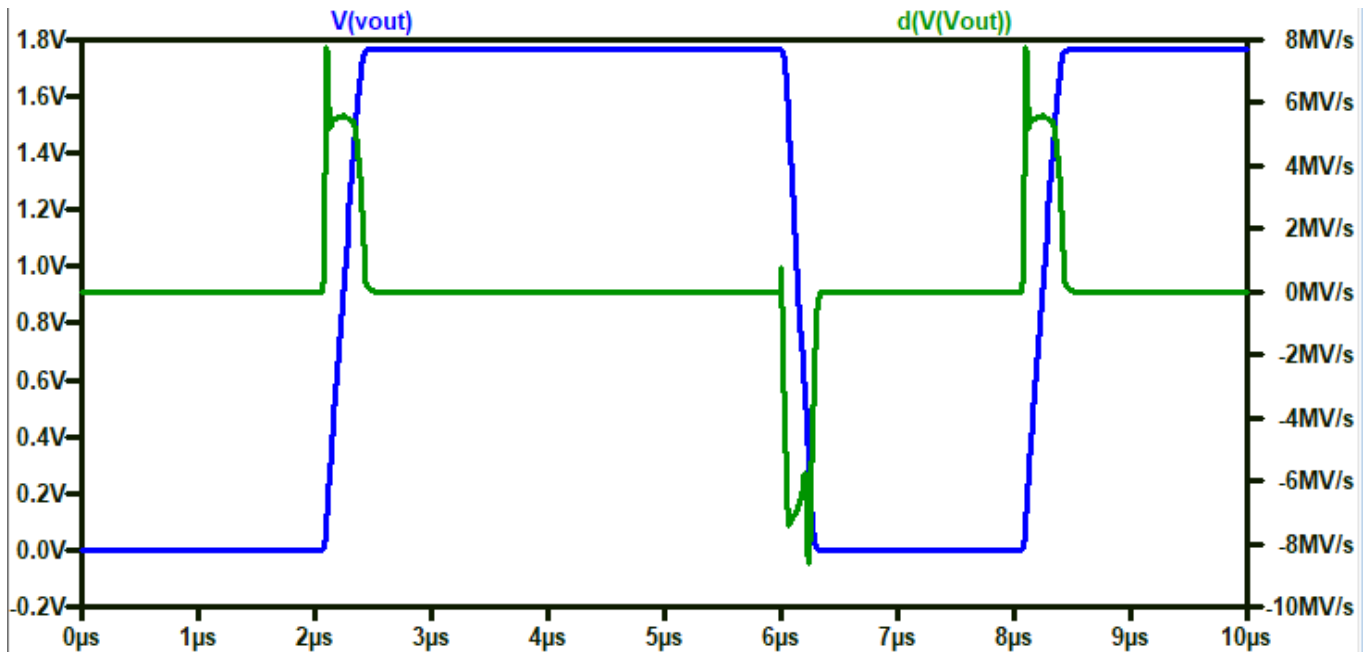


Figure 6



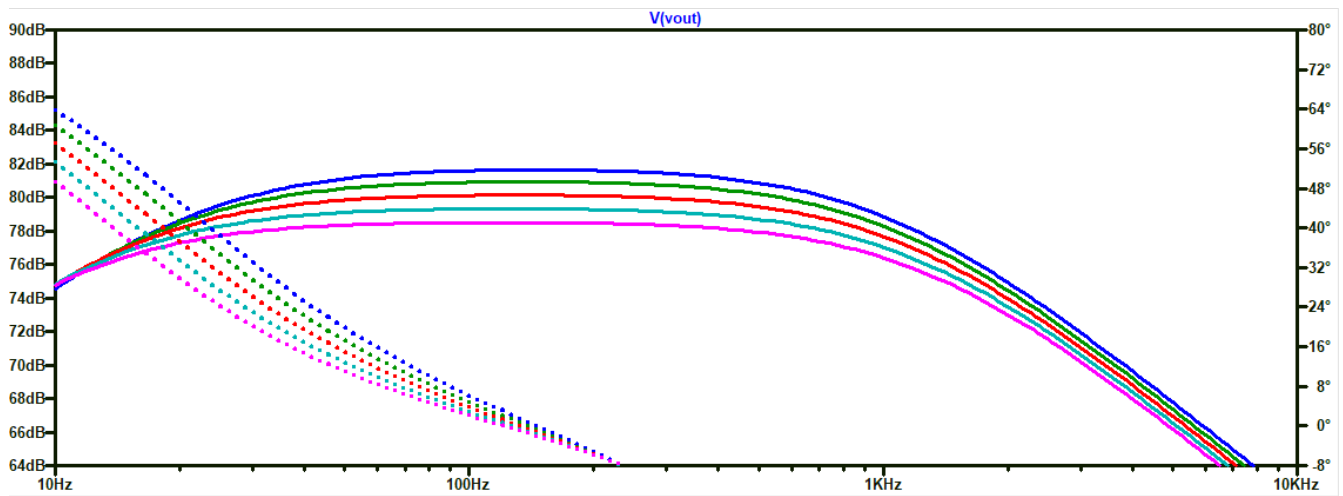
Step response shows some ringing but seems to be fine. See Sim\_StepResponse.asc. Slew rate is usually above  $5\text{V}/\mu\text{s}$  (Fig. 7) so we may have an over-engineered AB-type output buffer.

Figure 7



Another potential misstep is the failure of a few temperatures in a param list from 0 to 100 degrees to reach open-loop gain of 80dB as seen below.

**Figure 8**



## Power

The power simulation (Sim\_PowerConsumption.asc) shows current draw of about 1mA, but I recall that some of the AC simulations showed up to 75mA. It's not great, but better than it was before.

## Conclusion

I would have liked to try the OTA topology to see what it could do, but was essentially locked into this design by shortage of time.

## Table

VDD	Unity-gain Frequency	Slew Rate
2V	12MHz	5.1V/ $\mu$ s
3V	12MHz	6V/ $\mu$ s
4V	13.6MHz	6.2V/ $\mu$ s
5V	12.1MHz	~7V/ $\mu$ s

Note that negative slew rate (output toward ground is slightly faster).